

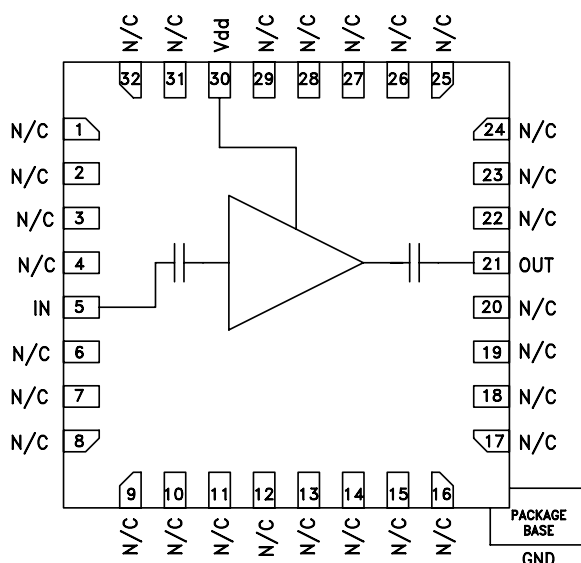
GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 2.0 - 20.0 GHz

Typical Applications

The HMC462LP5 Wideband LNA is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military EW, ECM & C³I
- Test Instrumentation
- Fiber Optics

Functional Diagram



Features

Noise Figure: 2.5 dB @ 10 GHz

Gain: 13 dB

P1dB Output Power: +14.5 dBm @ 10 GHz

Self-Biased: +5.0V @ 66 mA

50 Ohm Matched Input/Output

25 mm² Leadless SMT Package

General Description

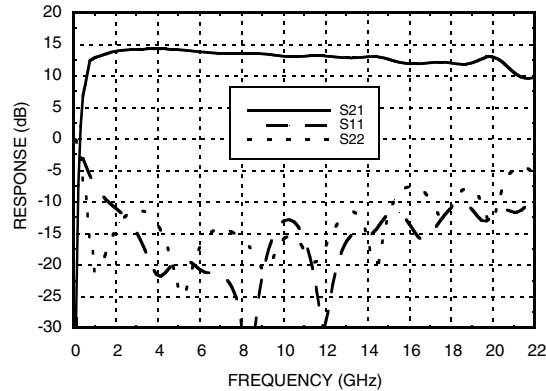
The HMC462LP5 is a GaAs MMIC PHEMT Low Noise Distributed Amplifier in a leadless 5 x 5 mm surface mount package which operates between 2 and 20 GHz. The self-biased amplifier provides 13 dB of gain, 2.5 to 3.5 dB noise figure and +14.5 dBm of output power at 1 dB gain compression while requiring only 66 mA from a single +5V supply. Gain flatness is excellent from 6 - 18 GHz making the HMC462LP5 ideal for EW, ECM RADAR and test equipment applications. The wideband amplifier I/Os are internally matched to 50 Ohms and are internally DC blocked.

Electrical Specifications, $T_A = +25^\circ \text{C}$, $V_{dd} = 5V$

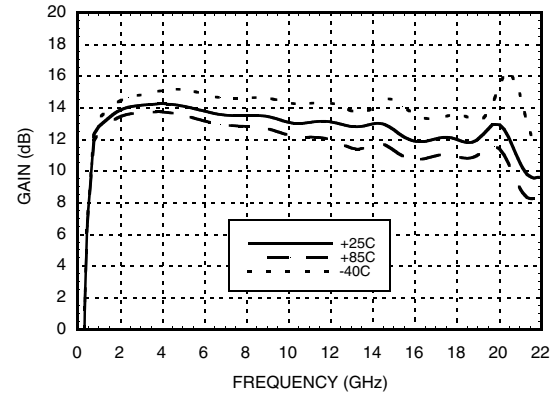
| Parameter | Min. | Typ. | Max. | Min. | Typ. | Max. | Min. | Typ. | Max. | Units |
|------------------------------------------|------|-----------|-------|------------|-----------|------|-------------|-----------|------|-------|
| Frequency Range | | 2.0 - 6.0 | | 6.0 - 14.0 | | | 14.0 - 20.0 | | | GHz |
| Gain | 12 | 14 | | 11 | 13 | | 10 | 12 | | dB |
| Gain Flatness | | ± 0.5 | | | ± 0.5 | | | ± 0.5 | | dB |
| Gain Variation Over Temperature | | 0.015 | 0.025 | | 0.02 | 0.03 | | 0.03 | 0.04 | dB/°C |
| Noise Figure | | 3.0 | 4.0 | | 2.5 | 4.0 | | 4.0 | 6.0 | dB |
| Input Return Loss | | 15 | | | 13 | | | 11 | | dB |
| Output Return Loss | | 12 | | | 12 | | | 8 | | dB |
| Output Power for 1 dB Compression (P1dB) | 12 | 15 | | 11 | 14 | | 9 | 12 | | dBm |
| Saturated Output Power (Psat) | | 17 | | | 16 | | | 15 | | dBm |
| Output Third Order Intercept (IP3) | | 26 | | | 25 | | | 22 | | dBm |
| Supply Current (Idd) (Vdd= 5V) | | 66 | | | 66 | | | 66 | | mA |

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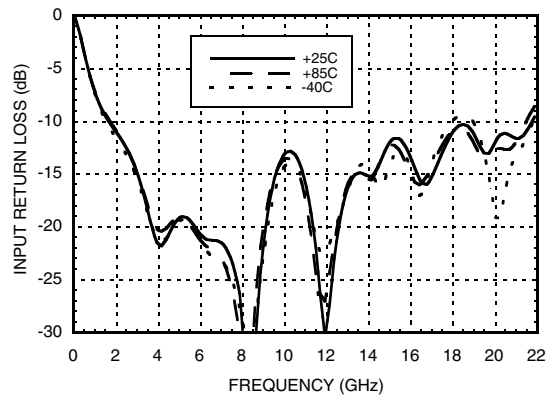
Gain & Return Loss



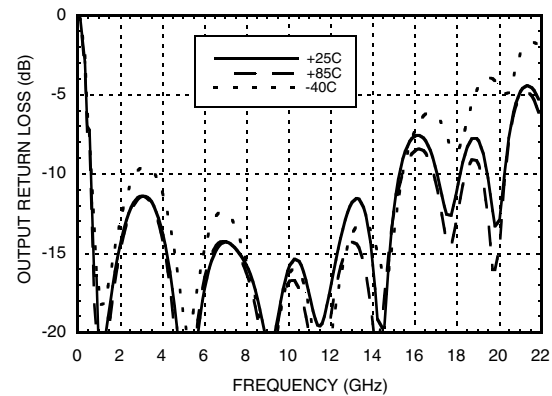
Gain vs. Temperature



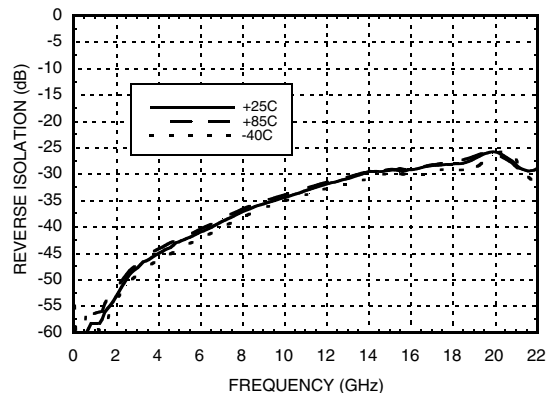
Input Return Loss vs. Temperature



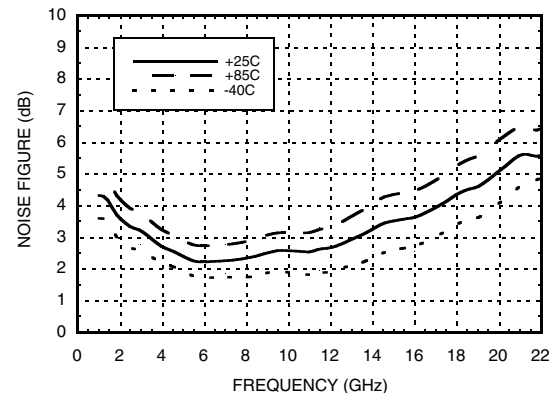
Output Return Loss vs. Temperature



Reverse Isolation vs. Temperature



Noise Figure vs. Temperature

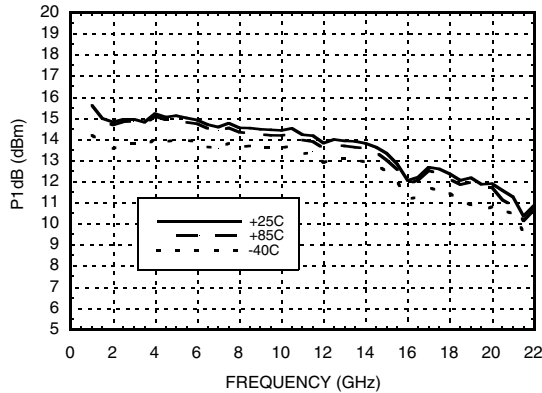


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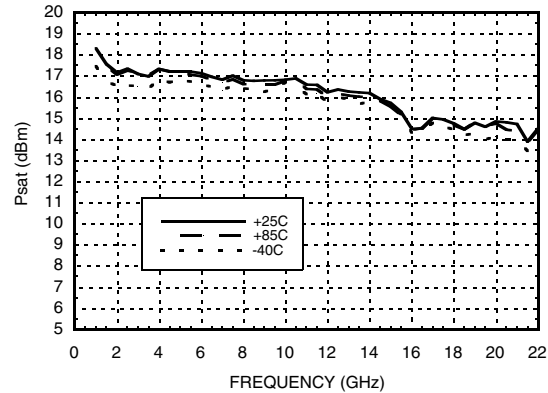
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AMPLIFIERS - SMT

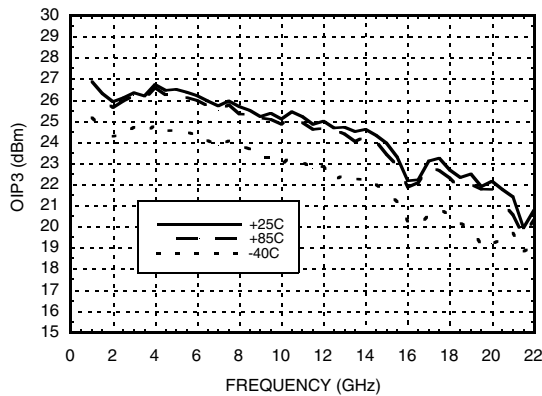
P1dB vs. Temperature



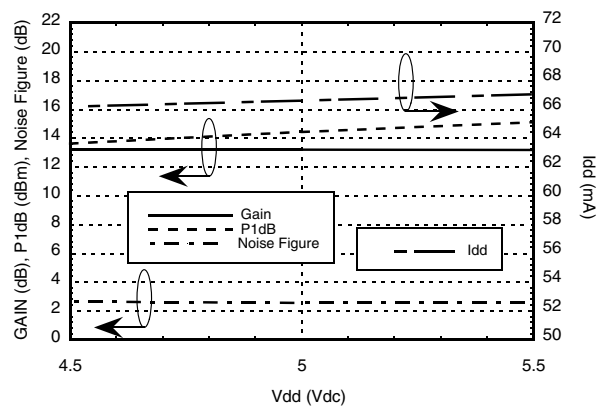
Psat vs. Temperature



Output IP3 vs. Temperature



Gain, Power, Noise Figure & Supply Current vs. Supply Voltage @ 10 GHz



Absolute Maximum Ratings

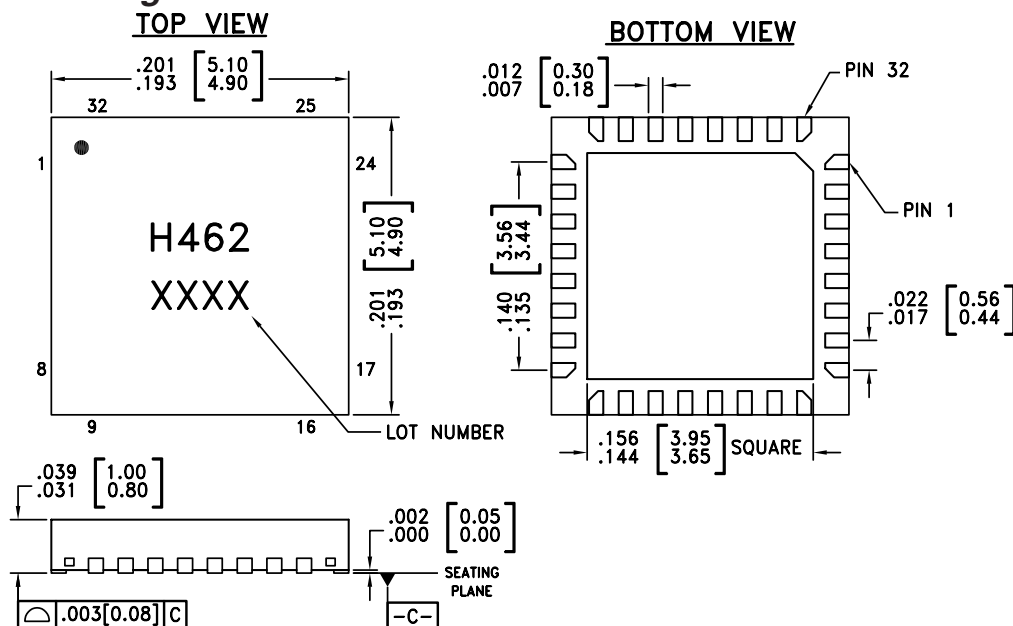
| | |
|---------------------------------------------------------------|----------------|
| Drain Bias Voltage (Vdd) | +9.0 Vdc |
| RF Input Power (RFIn)(Vdd = +5.0 Vdc) | +23 dBm |
| Channel Temperature | 150 °C |
| Continuous Pdiss (T = 85 °C) (derate 50 mW/°C above 85 °C) | 3.25 W |
| Thermal Resistance (channel to ground paddle) | 20 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |

Typical Supply Current vs. Vdd

| Vdd (V) | Idd (mA) |
|---------|----------|
| +4.5 | 66 |
| +5.0 | 67 |
| +5.5 | 68 |
| +7.5 | 71 |
| +8.0 | 72 |
| +8.5 | 73 |

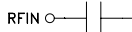
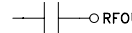
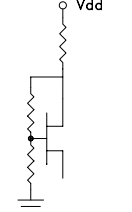
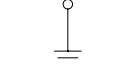
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Outline Drawing



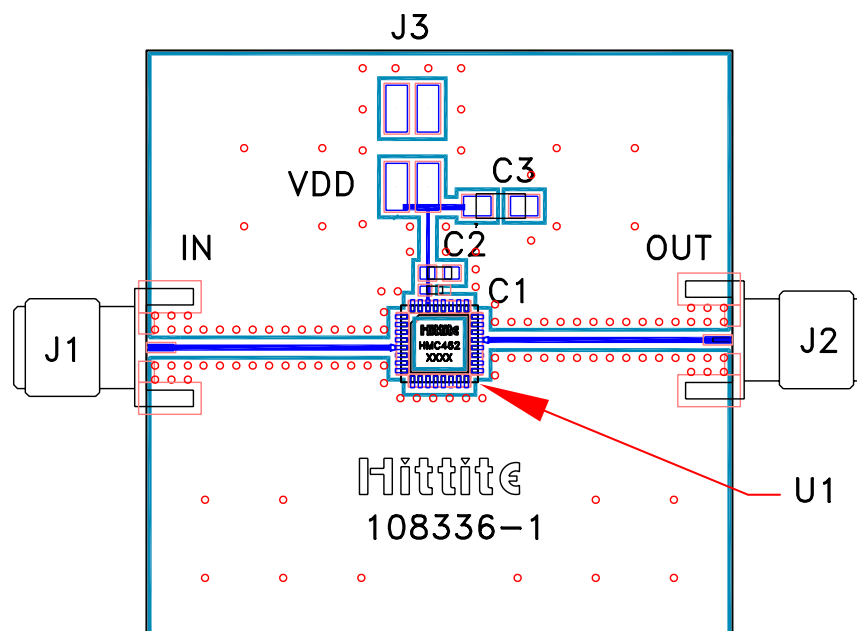
- NOTES:
1. ALL DIMENSIONS IN INCHES [MILLIMETERS]
 2. NO CONNECTION REQUIRED FOR UNLABELED BOND PADS
 3. DIE THICKNESS IS 0.004 (0.100)
 4. TYPICAL BOND PAD IS 0.004 (0.100) SQUARE
 5. BACKSIDE METALLIZATION: GOLD
 6. BACKSIDE METAL IS GROUND
 7. BOND PAD METALIZATION: GOLD

Pad Descriptions

| Pad Number | Function | Description | Interface Schematic |
|--------------------------|----------|--------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------|
| 5 | RFIN | This pad is AC coupled and matched to 50 Ohms from 2.0 - 20.0 GHz. | RFIN  |
| 21 | RFOUT | This pad is AC coupled and matched to 50 Ohms from 2.0 - 20.0 GHz. |  RFOUT |
| 30 | Vdd | Power supply voltage for the amplifier. External bypass capacitors are required. |  |
| Ground Paddle | GND | Ground paddle must be connected to RF/DC ground. |  |
| 1-4, 6-20, 22-29, 31, 32 | N/C | No connection. These pins may be connected to RF ground. Performance will not be affected. | |

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Evaluation PCB



List of Materials for Evaluation PCB 108338*

| Item | Description |
|----------------------------------------|---------------------------------|
| J1 - J2 | PC Mount SMA Connector |
| J3 | 2 mm Molex Header |
| C1 | 100 pF Capacitor, 0402 Pkg. |
| C2 | 1000 pF Capacitor, 0603 Pkg. |
| C3 | 4.7 μ F Capacitor, Tantalum |
| U1 | HMC462LP5 |
| PCB** | 108336 Evaluation PCB |
| ** Circuit Board Material: Rogers 4350 | |

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of VIA holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

* Reference this number when ordering complete evaluation PCB.

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Notes: